

10/553754

JC20 Rec'd PCT/PTO 18 OCT 2005

PATENT APPLICATION

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of

Makoto IIDA

Application No.: New U.S. National Stage of
PCT/JP04/006003

Filed: October 18, 2005

Docket No.: 125664

For: A METHOD FOR PRODUCING A SINGLE CRYSTAL AND A SINGLE CRYSTAL

INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

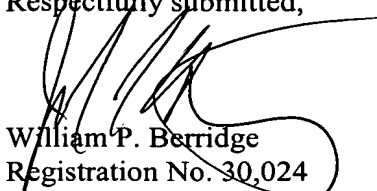
Pursuant to 37 CFR §1.56, the attention of the Patent and Trademark Office is hereby directed to the references listed on the attached PTO-1449. Unless otherwise indicated herein, one copy of each reference is attached. It is respectfully requested that the information be expressly considered during the prosecution of this application, and that the references be made of record therein and appear among the "References Cited" on any patent to issue therefrom.

- ☒ 1. This Information Disclosure Statement is being filed (a) within three months of the U.S. filing date of this non-CPA application, OR (b) before the mailing date of a first Office Action on the merits in the present application. No certification or fee is required.
- ☒ 2. Relevance of the English and non-English language references 4-8 is discussed in the present specification.
- ☒ 3. References 1-3 were cited in the International Search Report. An English language version of the International Search Report is attached for the Examiner's information.
- ☒ 4. English language Abstracts of the non-English language references 1-7 are attached hereto.

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- ☒ 5. A computer-generated English language translation of the following Japanese Patent Publication has been obtained from the website of the Japanese Patent Office (<http://www.jpo.go.jp>), and is attached, but has not been reviewed for accuracy. See References 1-7.

Respectfully submitted,


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Date: October 18, 2005

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Form PTO-1449 (REV. 8-83)		US Dept. of Commerce PATENT & TRADEMARK OFFICE		ATTY DOCKET NO. 125664		APPLICATION NO. New U.S. National Stage of PCT/JP04/006003 10/553754	
INFORMATION DISCLOSURE STATEMENT (Use several sheets if necessary)				APPLICANT Makoto IIDA			
				FILING DATE October 18, 2005			
U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	
FOREIGN PATENT DOCUMENTS							
		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB CLASS	
	1	JP A 2002-201093 w/abstr. & trans.	07/16/2002	JAPAN			
	2	JP A 2000-001391 w/abstr. & trans.	01/07/2000	JAPAN			
	3	JP A 09-263485 w/abstr. & trans.	10/07/1997	JAPAN			
	4	JP A 11-147786 w/abstr. & trans.	06/02/1999	JAPAN			
	5	JP A 2000-044388 w/abstr. & trans.	02/15/2000	JAPAN			
	6	JP A 11-349394 w/abstr. & trans.	12/21/1999	JAPAN			
	7	JP A 2002-057160 w/abstr. & trans.	02/22/2002	JAPAN			
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)							
	8	V.V. VORONOKOV; "The Mechanism of Swirl Defects Formation in Silicon"; Journal of Crystal Growth; Vol. 59; March 1982; pp. 625-643					
EXAMINER					DATE CONSIDERED		
Examiner: Initial if citation considered, whether or not citation is in conformance with M.P.E.P. 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.							

Date: October 18, 2005